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SFT1341

Power MOSFET -40V, 112mΩ, -10A, Single P-Channel

Features

- Low On-Resistance
- Low Gate Charge
- ESD Diode-Protected Gate
- High Speed Switching
- Low Gate Drive Voltage
- Pb-free and RoHS Compliance

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

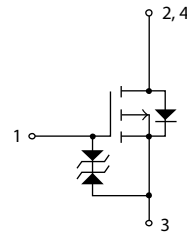
Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DSS}	-40	V
Gate to Source Voltage	V_{GSS}	± 10	V
Drain Current (DC)	I_D	-10	A
Drain Current $PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	I_{DP}	-40	A
Power Dissipation	P_D	1.0	W
		$T_c = 25^\circ\text{C}$	15
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal Resistance Ratings

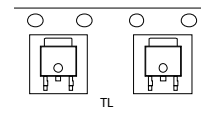
Parameter	Symbol	Value	Unit
Junction to Case Steady State	$R_{\theta JC}$	8.33	$^\circ\text{C/W}$
Junction to Ambient *1	$R_{\theta JA}$	125	

Note : *1 Insertion mounted

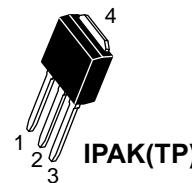
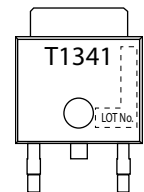
Electrical Connection P-Channel



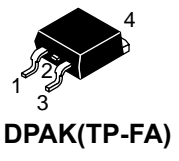
Packing Type: TL



Marking



IPAK (TP)



DPAK (TP-FA)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

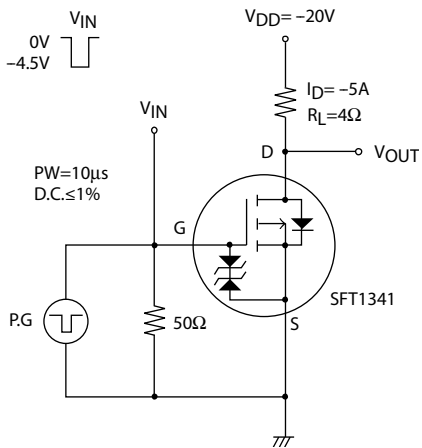
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Electrical Characteristics at $T_a = 25^\circ\text{C}$

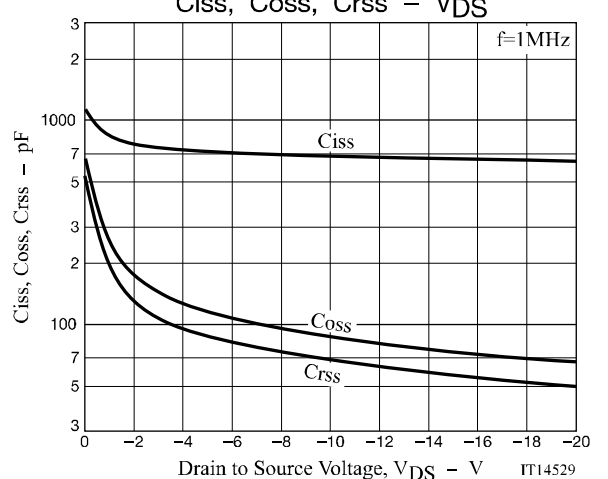
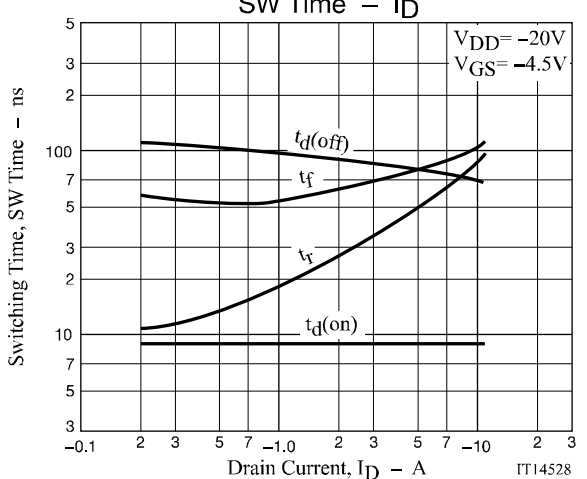
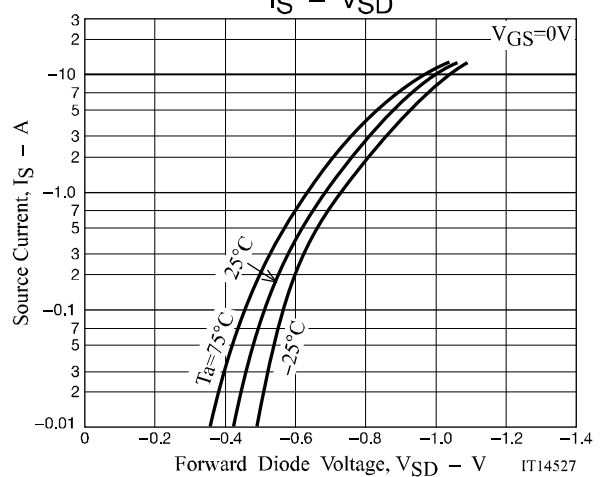
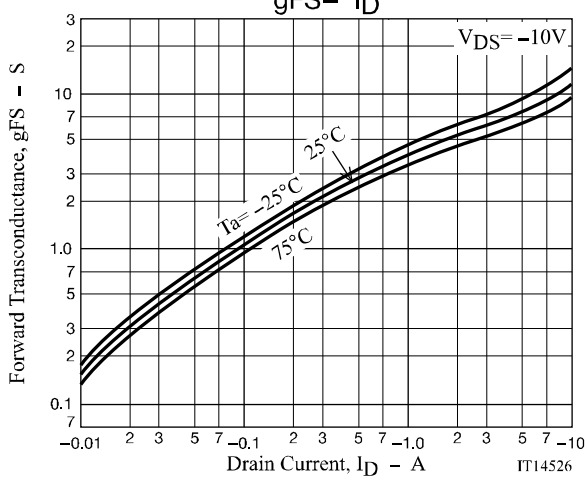
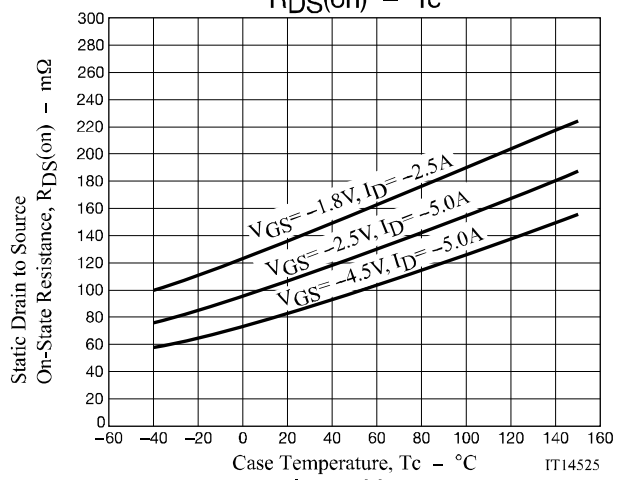
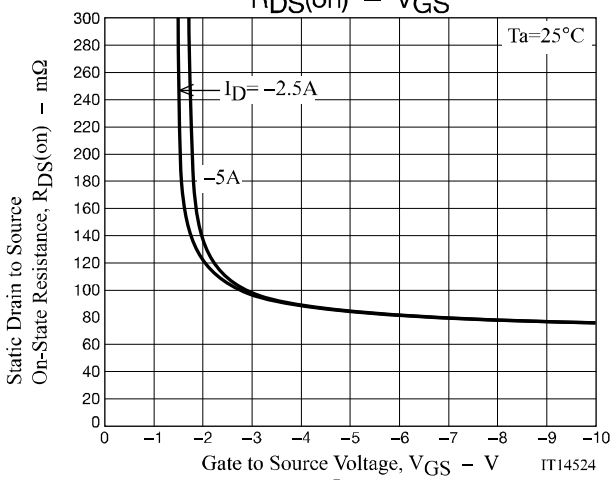
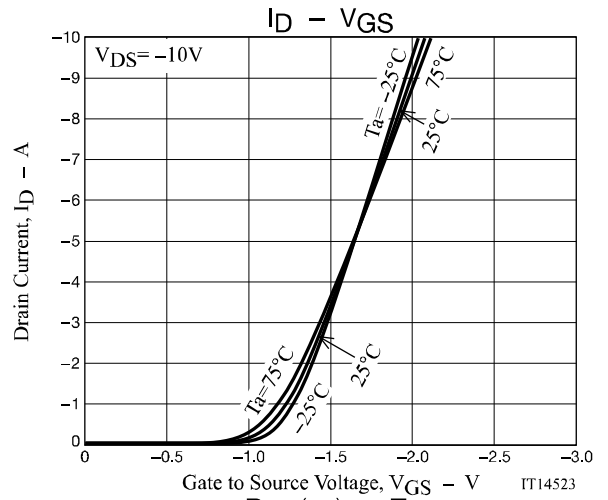
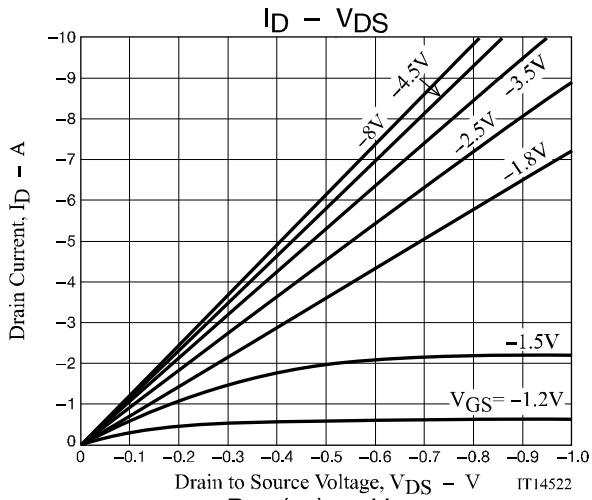
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0\text{V}$	-40			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -40\text{V}, V_{GS} = 0\text{V}$			-1	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-0.4		-1.4	V
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{V}, I_D = -5\text{A}$	4.6	7.7		S
Static Drain to Source On-State Resistance	$R_{DS(on)1}$	$I_D = -5\text{A}, V_{GS} = -4.5\text{V}$		86	112	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D = -5\text{A}, V_{GS} = -2.5\text{V}$		110	154	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D = -2.5\text{A}, V_{GS} = -1.8\text{V}$		140	210	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		650		pF
Output Capacitance	C_{oss}			65		pF
Reverse Transfer Capacitance	C_{rss}			50		pF
Turn-ON Delay Time	$t_{d(on)}$			9.0		ns
Rise Time	t_r	See specified Test Circuit.		50		ns
Turn-OFF Delay Time	$t_{d(off)}$			81		ns
Fall Time	t_f			80		ns
Total Gate Charge	Q_g			8.0		nC
Gate to Source Charge	Q_{gs}	$V_{DS} = -20\text{V}, V_{GS} = -4.5\text{V}, I_D = -10\text{A}$		1.4		nC
Gate to Drain "Miller" Charge	Q_{gd}			2.5		nC
Forward Diode Voltage	V_{SD}		$I_S = -10\text{A}, V_{GS} = 0\text{V}$		-1.0	-1.5

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

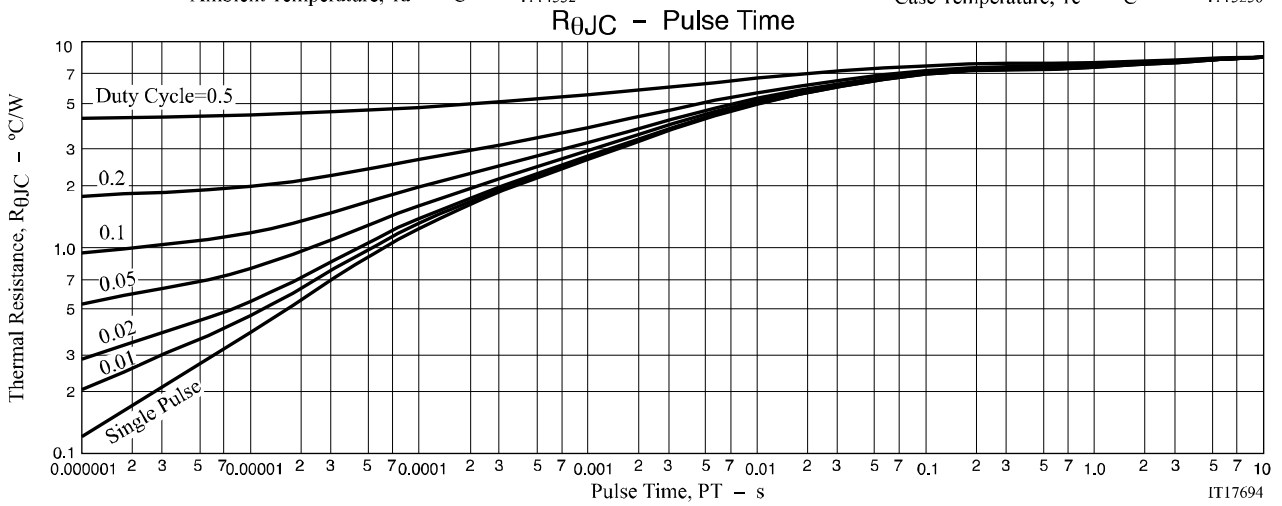
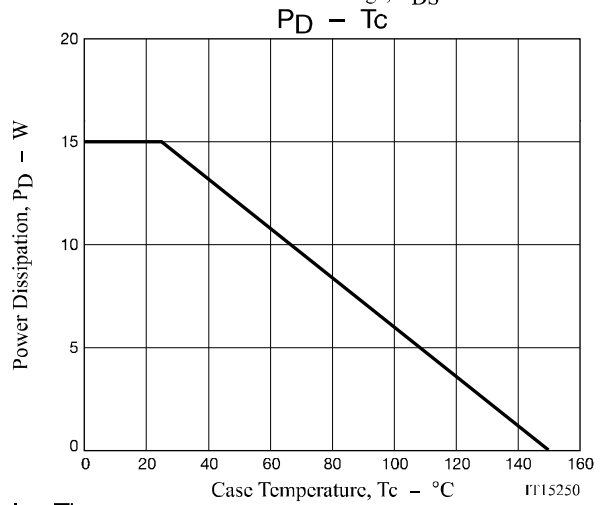
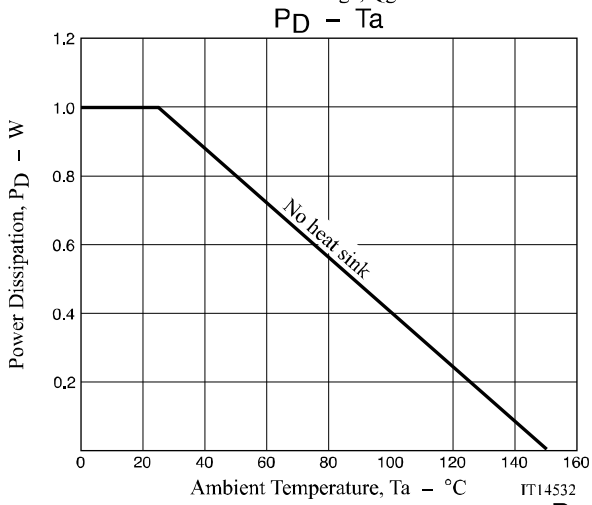
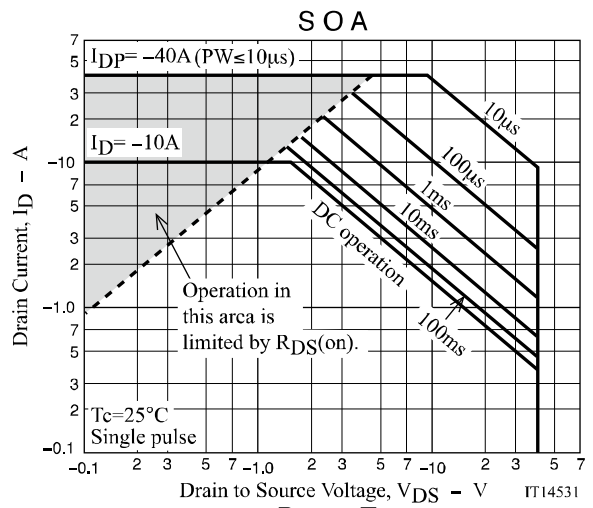
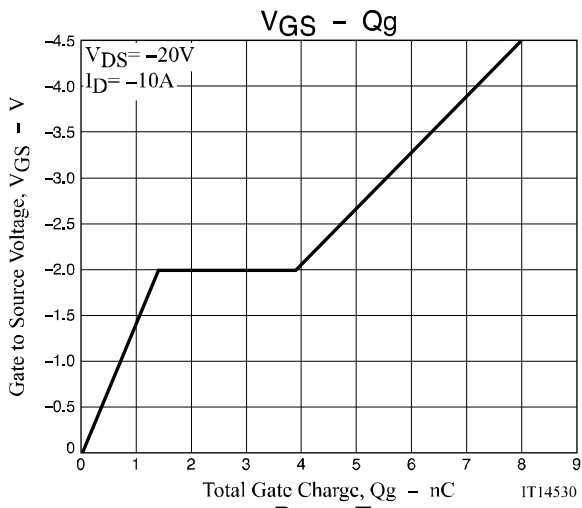
Switching Time Test Circuit



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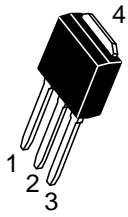
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Package Dimensions

SFT1341-E/ SFT1341-W

IPAK/TP

Unit : mm

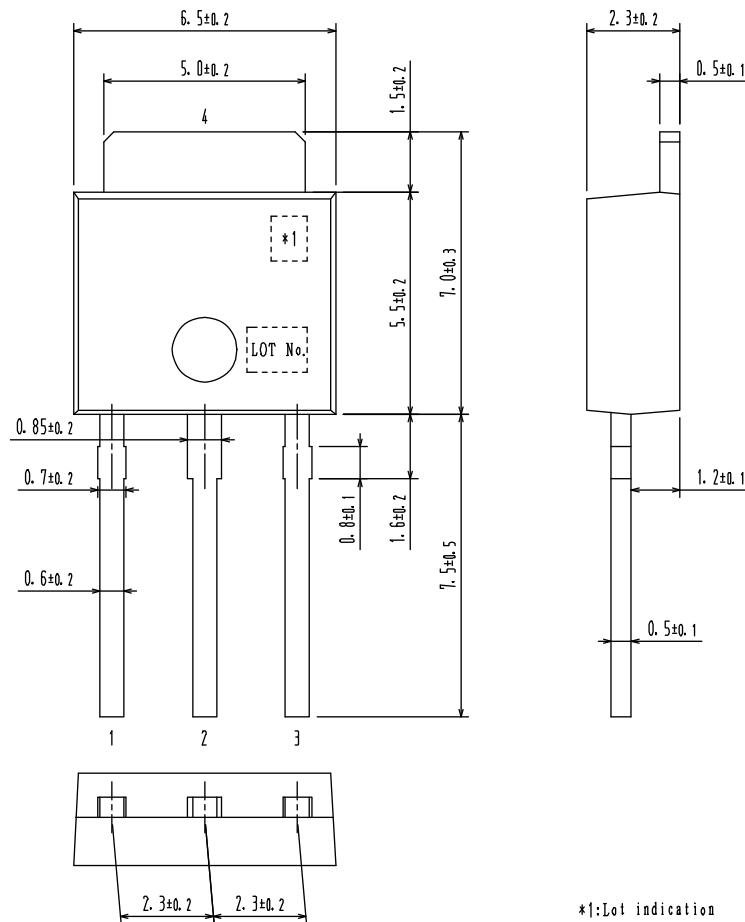


1:Gate

2:Drain

3:Source

4:Drain



Ordering & Package Information

Device	Package	Shipping	Note
SFT1341-E	IPAK(TP)	500pcs. / bag	Pb-Free
SFT1341-W	SC-64 TO-251		Pb-Free and Halogen Free
SFT1341-TL-E	DPAK(TP-FA)	700pcs. / reel	Pb-Free
SFT1341-TL-W	SC-63 TO-252		Pb-Free and Halogen Free

Note on usage : Since the SFT1341 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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